



# PSMN9R5-100PS

N-channel 100 V 9.6 mΩ standard level MOSFET in TO220

17 October 2013

Product data sheet

## 1. General description

Standard level N-channel MOSFET in a TO220 packages qualified to 175°C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

## 3. Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

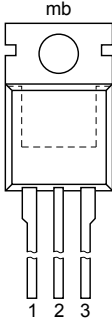
## 4. Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                                    | Conditions                                                                                                                               |  | Min | Typ  | Max | Unit |
|-------------------------|----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|------|
| V <sub>DS</sub>         | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C                                                                                          |  | -   | -    | 100 | V    |
| I <sub>D</sub>          | drain current                                | T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <a href="#">Fig. 1</a>                                                                  |  | -   | -    | 89  | A    |
| P <sub>tot</sub>        | total power dissipation                      | T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>                                                                                          |  | -   | -    | 211 | W    |
| Static characteristics  |                                              |                                                                                                                                          |  |     |      |     |      |
| R <sub>DSon</sub>       | drain-source on-state resistance             | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a>                                           |  | -   | 8.16 | 9.6 | mΩ   |
| Dynamic characteristics |                                              |                                                                                                                                          |  |     |      |     |      |
| Q <sub>GD</sub>         | gate-drain charge                            | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 60 A; V <sub>DS</sub> = 50 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>                 |  | -   | 23   | -   | nC   |
| Q <sub>G(tot)</sub>     | total gate charge                            |                                                                                                                                          |  | -   | 82   | -   | nC   |
| Avalanche ruggedness    |                                              |                                                                                                                                          |  |     |      |     |      |
| E <sub>DS(AL)S</sub>    | non-repetitive drain-source avalanche energy | V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 89 A; V <sub>sup</sub> ≤ 100 V; unclamped; R <sub>GS</sub> = 50 Ω |  | -   | -    | 177 | mJ   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                        | Graphic symbol                                                                      |
|-----|--------|-----------------------------------|-----------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | G      | gate                              |  <p>TO-220AB (SOT78)</p> |  |
| 2   | D      | drain                             |                                                                                                           |                                                                                     |
| 3   | S      | source                            |                                                                                                           |                                                                                     |
| mb  | D      | mounting base; connected to drain |                                                                                                           |                                                                                     |

## 6. Ordering information

Table 3. Ordering information

| Type number   | Package  |                                                                                  |         |
|---------------|----------|----------------------------------------------------------------------------------|---------|
|               | Name     | Description                                                                      | Version |
| PSMN9R5-100PS | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

## 7. Marking

Table 4. Marking codes

| Type number   | Marking code  |
|---------------|---------------|
| PSMN9R5-100PS | PSMN9R5-100PS |

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter            | Conditions                                                                        | Min | Max | Unit |
|-----------|----------------------|-----------------------------------------------------------------------------------|-----|-----|------|
| $V_{DS}$  | drain-source voltage | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                | -   | 100 | V    |
| $V_{DGR}$ | drain-gate voltage   | $T_j \leq 175\text{ °C}$ ; $T_j \geq 25\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$ | -   | 100 | V    |
| $V_{GS}$  | gate-source voltage  |                                                                                   | -20 | 20  | V    |
| $I_D$     | drain current        | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 1                        | -   | 63  | A    |
|           |                      | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 1                         | -   | 89  | A    |
| $I_{DM}$  | peak drain current   | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 3       | -   | 355 | A    |

| Symbol               | Parameter                                    | Conditions                                                                                                                                  |  | Min | Max | Unit |
|----------------------|----------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------|--|-----|-----|------|
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>                                                                                             |  | -   | 211 | W    |
| T <sub>stg</sub>     | storage temperature                          |                                                                                                                                             |  | -55 | 175 | °C   |
| T <sub>j</sub>       | junction temperature                         |                                                                                                                                             |  | -55 | 175 | °C   |
| T <sub>sld(M)</sub>  | peak soldering temperature                   |                                                                                                                                             |  | -   | 260 | °C   |
| Source-drain diode   |                                              |                                                                                                                                             |  |     |     |      |
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C                                                                                                                     |  | -   | 89  | A    |
| I <sub>SM</sub>      | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C                                                                                     |  | -   | 355 | A    |
| Avalanche ruggedness |                                              |                                                                                                                                             |  |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 89 A;<br>V <sub>sup</sub> ≤ 100 V; unclamped; R <sub>GS</sub> = 50 Ω |  | -   | 177 | mJ   |

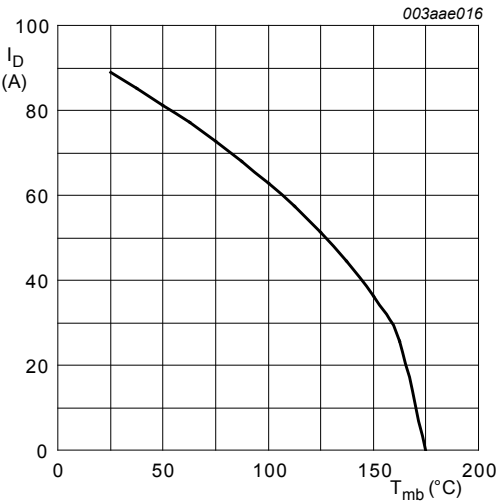


Fig. 1. Continuous drain current as a function of mounting base temperature

$V_{GS} \geq 10\text{ V}$

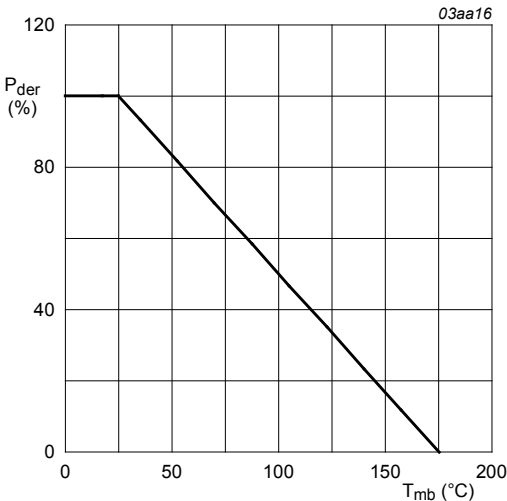


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

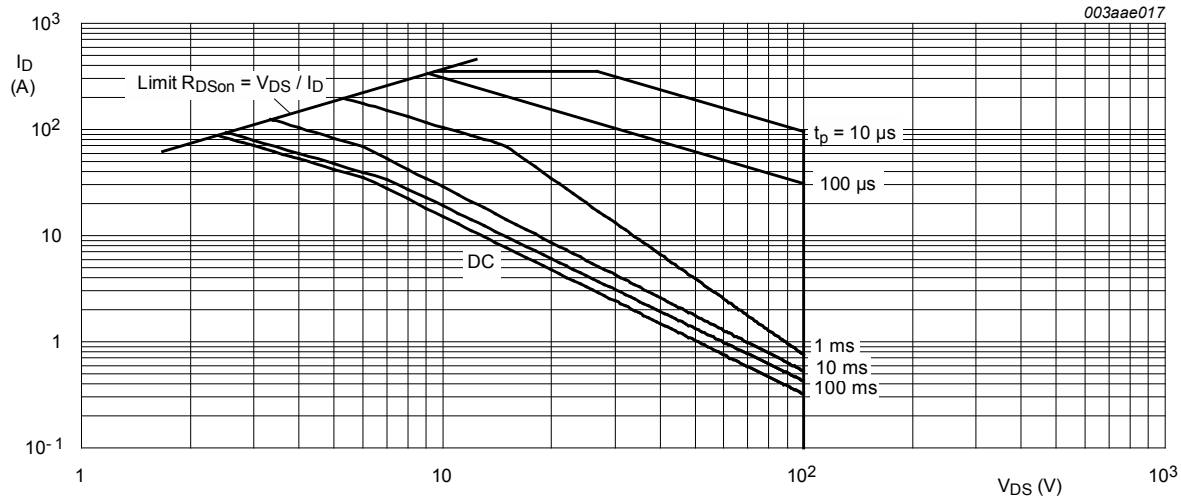


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25\text{ }^{\circ}\text{C}; I_{DM}$  is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 4     | -   | 0.38 | 0.71 | K/W  |

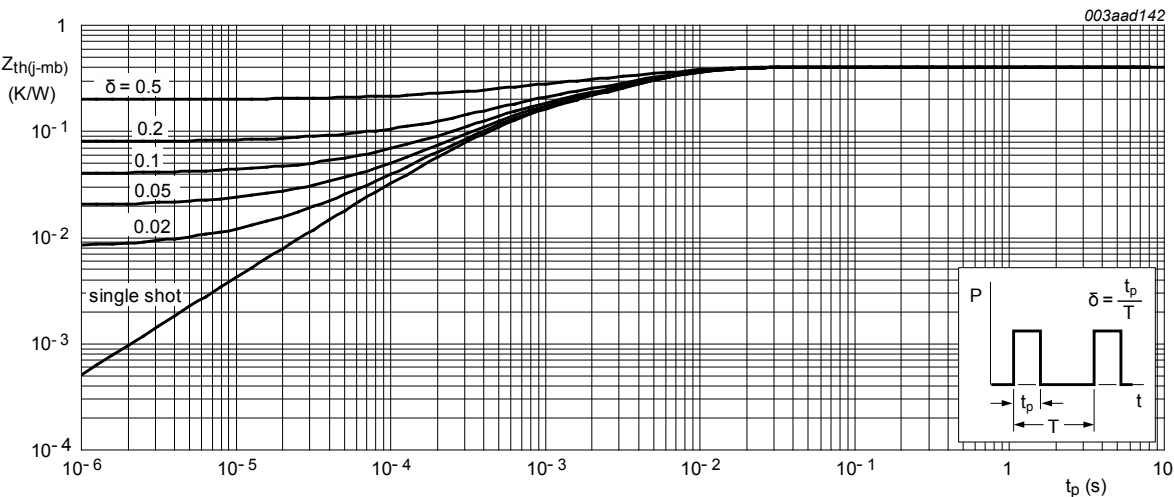


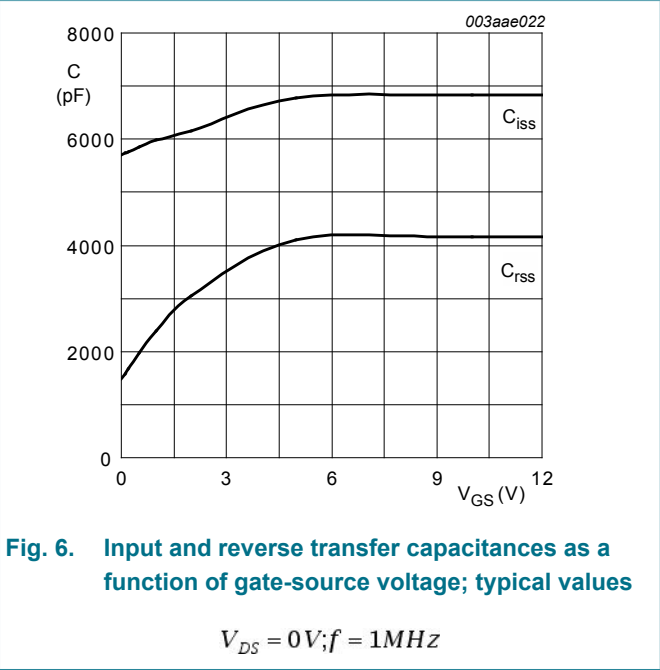
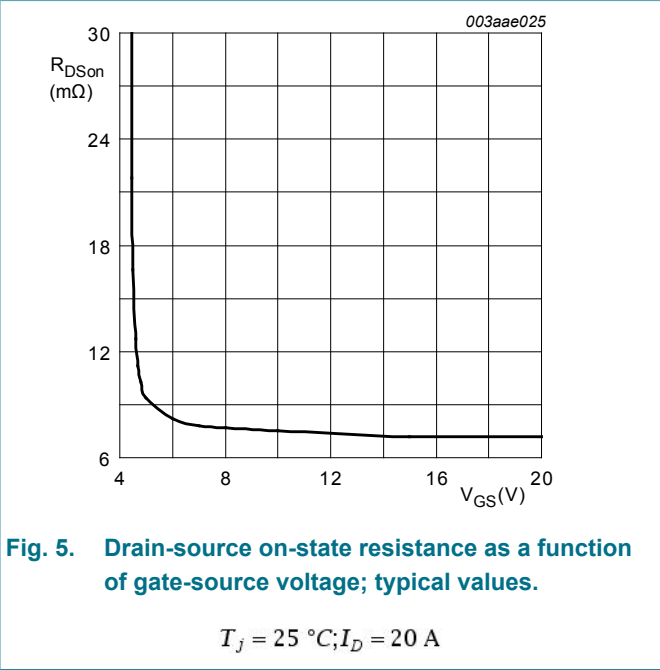
Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter                         | Conditions                                                                                                                        |  | Min | Typ  | Max  | Unit          |
|--------------------------------|-----------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|---------------|
| <b>Static characteristics</b>  |                                   |                                                                                                                                   |  |     |      |      |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage    | $I_D = 0.25 \text{ mA}$ ; $V_{GS} = 0 \text{ V}$ ; $T_J = -55 \text{ }^\circ\text{C}$                                             |  | 90  | -    | -    | V             |
|                                |                                   | $I_D = 0.25 \text{ mA}$ ; $V_{GS} = 0 \text{ V}$ ; $T_J = 25 \text{ }^\circ\text{C}$                                              |  | 100 | -    | -    | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage     | $I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_J = 175 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a> |  | 1   | -    | -    | V             |
|                                |                                   | $I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_J = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>  |  | 2   | 3    | 4    | V             |
|                                |                                   | $I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_J = -55 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a> |  | -   | -    | 4.8  | V             |
| $I_{DSS}$                      | drain leakage current             | $V_{DS} = 100 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_J = 125 \text{ }^\circ\text{C}$                                            |  | -   | -    | 100  | $\mu\text{A}$ |
|                                |                                   | $V_{DS} = 100 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_J = 25 \text{ }^\circ\text{C}$                                             |  | -   | 0.02 | 4    | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current              | $V_{GS} = 20 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_J = 25 \text{ }^\circ\text{C}$                                              |  | -   | 10   | 100  | nA            |
|                                |                                   | $V_{GS} = -20 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_J = 25 \text{ }^\circ\text{C}$                                             |  | -   | 10   | 100  | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance  | $V_{GS} = 10 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_J = 100 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                     |  | -   | -    | 17.3 | mΩ            |
|                                |                                   | $V_{GS} = 10 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_J = 175 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                     |  | -   | 23.5 | 27.4 | mΩ            |
|                                |                                   | $V_{GS} = 10 \text{ V}$ ; $I_D = 15 \text{ A}$ ; $T_J = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 13</a>                      |  | -   | 8.16 | 9.6  | mΩ            |
| $R_G$                          | internal gate resistance (AC)     | $f = 1 \text{ MHz}$                                                                                                               |  | -   | 0.7  | -    | Ω             |
| <b>Dynamic characteristics</b> |                                   |                                                                                                                                   |  |     |      |      |               |
| $Q_{G(tot)}$                   | total gate charge                 | $I_D = 0 \text{ A}$ ; $V_{DS} = 0 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 14</a>                                  |  | -   | 67   | -    | nC            |
|                                |                                   | $I_D = 60 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>      |  | -   | 82   | -    | nC            |
| $Q_{GS}$                       | gate-source charge                |                                                                                                                                   |  | -   | 21   | -    | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge  | $I_D = 60 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 3 \text{ V}$ ; <a href="#">Fig. 14</a>                                 |  | -   | 13.1 | -    | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge | $I_D = 60 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 14</a>                                |  | -   | 7.8  | -    | nC            |
| $Q_{GD}$                       | gate-drain charge                 | $I_D = 60 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>      |  | -   | 23   | -    | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage       | $V_{DS} = 50 \text{ V}$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>                                                       |  | -   | 4.5  | -    | V             |
| $C_{iss}$                      | input capacitance                 | $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $f = 1 \text{ MHz}$ ;                                                          |  | -   | 4454 | -    | pF            |
| $C_{oss}$                      | output capacitance                | $T_J = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a>                                                                       |  | -   | 302  | -    | pF            |

| Symbol              | Parameter                    | Conditions                                                                                                                     |  | Min | Typ  | Max | Unit |
|---------------------|------------------------------|--------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|------|
| C <sub>rss</sub>    | reverse transfer capacitance |                                                                                                                                |  | -   | 185  | -   | pF   |
| t <sub>d(on)</sub>  | turn-on delay time           | V <sub>DS</sub> = 50 V; R <sub>L</sub> = 0.8 Ω; V <sub>GS</sub> = 10 V;<br>R <sub>G(ext)</sub> = 4.7 Ω; T <sub>j</sub> = 25 °C |  | -   | 22   | -   | ns   |
| t <sub>r</sub>      | rise time                    |                                                                                                                                |  | -   | 25.2 | -   | ns   |
| t <sub>d(off)</sub> | turn-off delay time          |                                                                                                                                |  | -   | 52.2 | -   | ns   |
| t <sub>f</sub>      | fall time                    |                                                                                                                                |  | -   | 22.8 | -   | ns   |
| Source-drain diode  |                              |                                                                                                                                |  |     |      |     |      |
| V <sub>SD</sub>     | source-drain voltage         | I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a>                                  |  | -   | 0.85 | 1.2 | V    |
| t <sub>rr</sub>     | reverse recovery time        | I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = 100 A/μs; V <sub>GS</sub> = 0 V;<br>V <sub>DS</sub> = 50 V                        |  | -   | 61.5 | -   | ns   |
| Q <sub>r</sub>      | recovered charge             |                                                                                                                                |  | -   | 157  | -   | nC   |



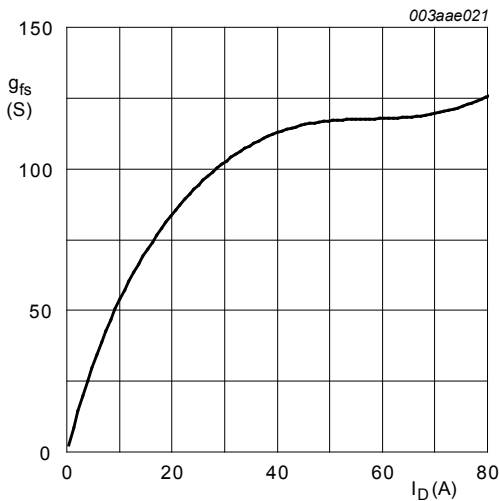


Fig. 7. Forward transconductance as a function of drain current; typical values

$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 25\text{ V}$

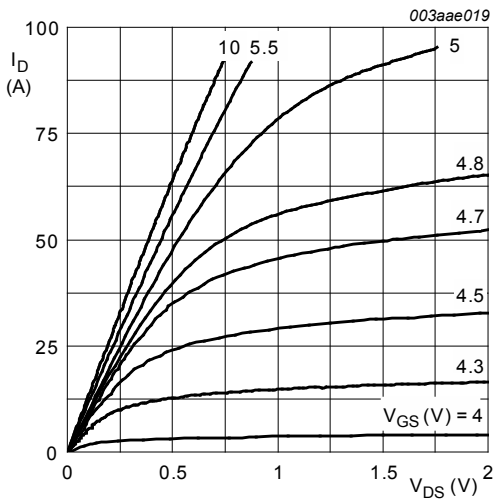


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}$

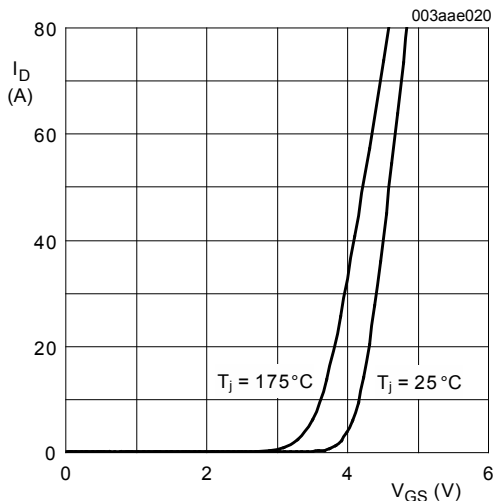


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} > I_D \times R_{DSon}$

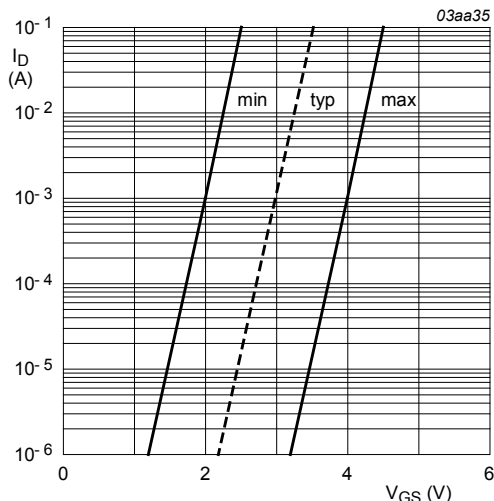


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

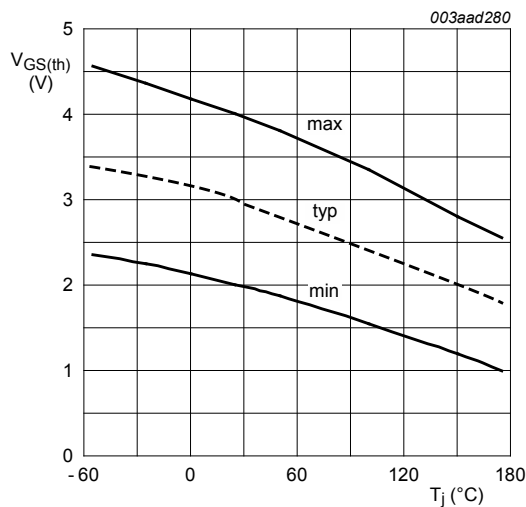


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

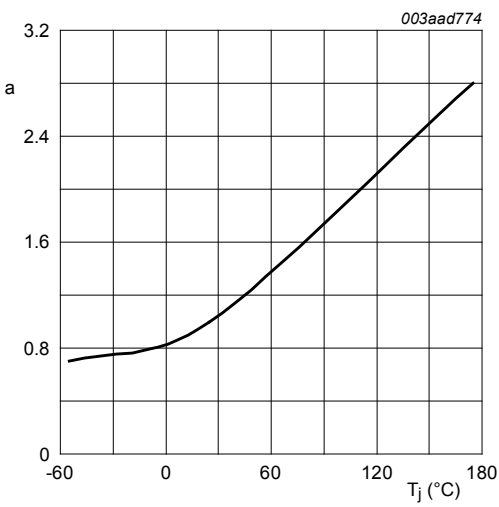


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)25\text{ °C}}}$$

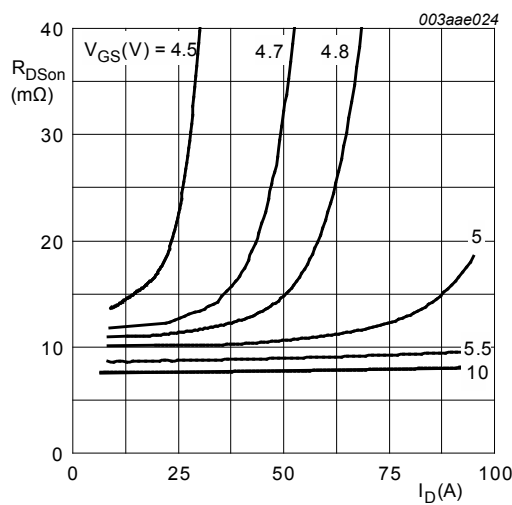


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25\text{ °C}$$

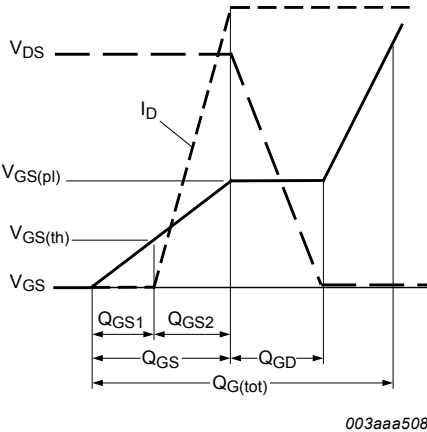


Fig. 14. Gate charge waveform definitions

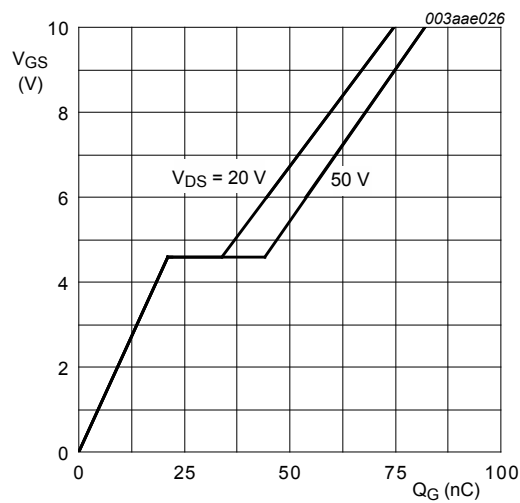


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_J = 25\text{ °C}$ ;  $I_D = 60\text{ A}$

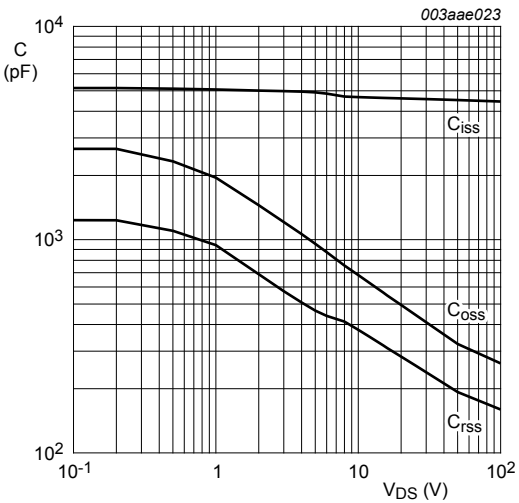


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}$ ;  $f = 1\text{ MHz}$

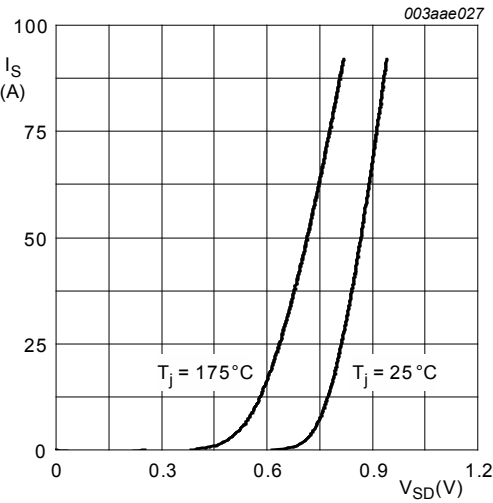


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\text{ V}$

11. Package outline



Fig. 18. Package outline TO-220AB (SOT78)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

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